Amendments to the Claims:

Listing of Claims:

Claims 1-241 (canceled)

242. (currently amended) A method for fabricating a chip package comprising:

joining a die and a substrate, wherein said die has ~~having~~ a top surface at a horizontal level, wherein said die and said substrate are under said horizontal level;

after said joining said die and said substrate, forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends ~~extending~~ across an edge of said die;

after said joining said die and said substrate, forming a passive device over said substrate and over said horizontal level, wherein said passive device comprises a part ~~is entirely~~ not directly over ~~said~~ any die; and

after said forming said patterned circuit layer and said forming said passive device, separating said substrate into multiple portions.

243. (currently amended) A method for fabricating a chip package comprising:

providing a first die having a first top surface at a horizontal level;

providing a second die having a second top surface at said horizontal level;

forming a polymer between said first and second dies;

~~joining a die and a substrate, said die having a top surface at horizontal level, wherein said die and said substrate are under said horizontal level;~~

~~after said joining said die and said substrate,~~ after said forming said polymer, forming a passive device over said horizontal level, wherein said passive device has ~~having~~ a first connection point connected to said first die; and

after said forming said passive device, forming a metal bump over said horizontal level, wherein said metal bump is connected to a second connection point of said passive device. ~~; and~~

~~separating said substrate into multiple portions.~~

244. (currently amended) A method for fabricating a chip package comprising:

providing a first die having a first top surface at a horizontal level;

providing a second die having a second top surface at said horizontal level;

forming a polymer between said first and second dies;

after said forming said polymer, forming a passive device over said horizontal level, wherein said passive device has a ~~portion~~ part not directly over any die; ~~said first and second dies;~~

after said forming said passive device over said horizontal level, forming an insulating layer on said passive device; and

after said forming said polymer, forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends across an edge of said first or second die.

245. (previously presented) The method of claim 242, wherein said substrate comprises a metal substrate.

246. (currently amended) The method of claim 242 further comprising joining a film and said substrate, wherein an opening in said film exposes ~~exposing~~ said substrate, followed by said joining said die and said substrate exposed by said opening.

247. (currently amended) The method of claim 246, wherein forming said opening in said film ~~comprising~~ comprises a punching process.

248. (previously presented) The method of claim 246, wherein said film comprises a metal layer.

Claim 249 (canceled)

250. (previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises an electroplating process.

251. (previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises a sputtering process.

252. (previously presented) The method of claim 242, wherein said forming said passive device comprises an electroplating process.

253. (withdrawn) The method of claim 242, wherein said forming said passive device comprises a sputtering process.

254. (previously presented) The method of claim 242, after said joining said die and said substrate, further comprising forming a solder bump over said horizontal level, followed by said separating said substrate.

255. (withdrawn) The method of claim 242, after said joining said die and said substrate, further comprising forming a gold bump over said horizontal level, followed by said separating said substrate.

256. (currently amended) The method of claim 242, wherein said passive device comprises an inductor. ~~forming said patterned circuit layer and said forming said passive device are followed by said separating said substrate.~~

257. (currently amended) The method of claim 243 further comprising joining said first die and a substrate and joining said second die and said substrate, followed by said forming said polymer. ~~, wherein said substrate comprises a metal substrate.~~

258. (currently amended) The method of claim 257, ~~243~~ wherein said substrate comprises a metal substrate. ~~further comprising joining a film and said substrate,~~

~~an opening in said film exposing said substrate, followed by said joining said die and said substrate exposed by said opening.~~

259. (currently amended) The method of claim 257, ~~258,~~ after said forming said metal bump, further comprising separating said substrate into multiple portions. ~~wherein forming said opening in said film comprising a punching process.~~

260. (currently amended) The method of claim 243, ~~258,~~ wherein said polymer comprises an epoxy. ~~film comprises a metal layer.~~

261. (currently amended) The method of claim 243, after said forming said polymer, ~~joining said die and said substrate,~~ further comprising forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends ~~extending~~ across an edge of said first die, followed by said forming said metal bump. ~~separating said substrate.~~

262. (previously presented) The method of claim 261, wherein said forming said patterned circuit layer comprises an electroplating process.

263. (previously presented) The method of claim 261, wherein said forming said patterned circuit layer comprises a sputtering process.

264. (previously presented) The method of claim 243, wherein said forming said passive device comprises an electroplating process.

265. (withdrawn) The method of claim 243, wherein said forming said passive device comprises a sputtering process.

266. (previously presented) The method of claim 243, wherein said forming said metal bump comprises forming a solder bump over said horizontal level, wherein said solder bump is connected to said second connection point.

267. (withdrawn) The method of claim 243, wherein said forming said metal bump comprises forming a gold bump over said horizontal level, wherein said gold bump is connected to said second connection point.

268. (currently amended) The method of claim 243, wherein said passive device comprises an inductor. ~~forming said metal bump is followed by said separating said substrate.~~

269. (previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises an electroplating process.

270. (previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises a sputtering process.

271. (previously presented) The method of claim 244, wherein said forming said passive device comprises an electroplating process.

272. (withdrawn) The method of claim 244, wherein said forming said passive device comprises a sputtering process.

273. (previously presented) The method of claim 244, after said forming said insulating layer and said forming said patterned circuit layer, further comprising forming a solder bump over said horizontal level.

274. (withdrawn) The method of claim 244, after said forming said insulating layer and said forming said patterned circuit layer, further comprising forming a gold bump over said horizontal level.

275. (new) The method of claim 244, wherein said passive device comprises an inductor.

276. (new) The method of claim 244, wherein said passive device comprises a capacitor.

277. (new) The method of claim 244, wherein said passive device comprises a resistor.

278. (new) The method of claim 244, wherein said passive device comprises a filter.

279. (new) The method of claim 244, wherein said polymer comprises an epoxy.

280. (new) The method of claim 244 further comprising joining said first die and a substrate and joining said second die and said substrate, followed by said forming said polymer.

281. (new) The method of claim 280, wherein said substrate comprises a metal substrate.

282. (new) The method of claim 280, after said forming said insulating layer and said forming said patterned circuit layer, further comprising separating said substrate into multiple portions.

283. (new) The method of claim 242, wherein said passive device comprises a capacitor.

284. (new) The method of claim 242, wherein said passive device comprises a resistor.

285. (new) The method of claim 242, wherein said passive device comprises a filter.

286. (new) The method of claim 243, wherein said passive device comprises a capacitor.

287. (new) The method of claim 243, wherein said passive device comprises a resistor.

288. (new) The method of claim 243, wherein said passive device comprises a filter.